

Supplementary Page

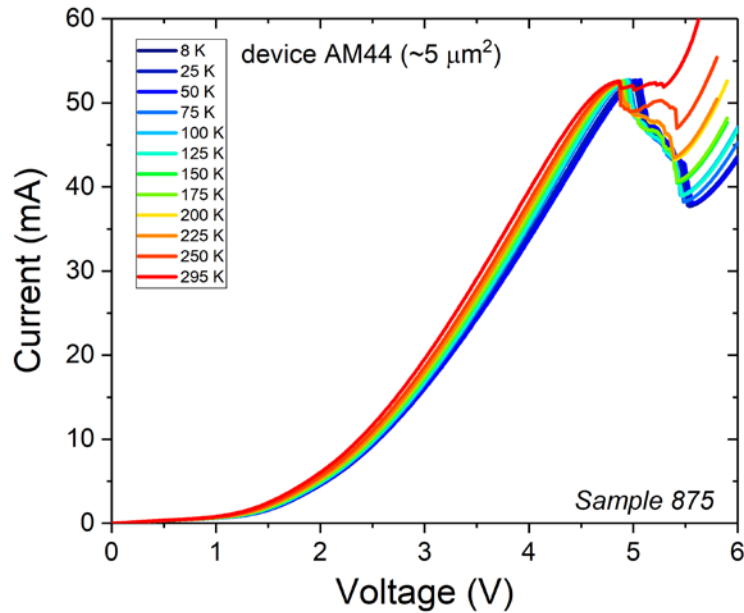


Figure 1. Temperature-dependent current-voltage curves of an AlN/GaN RTD grown at 860 °C on a GaN-templated sapphire wafer. The device area is $\sim 5 \mu\text{m}^2$. The NDR region is visible at $\sim 5\text{V}$, and the NDR persists up to room temperature (295 K).

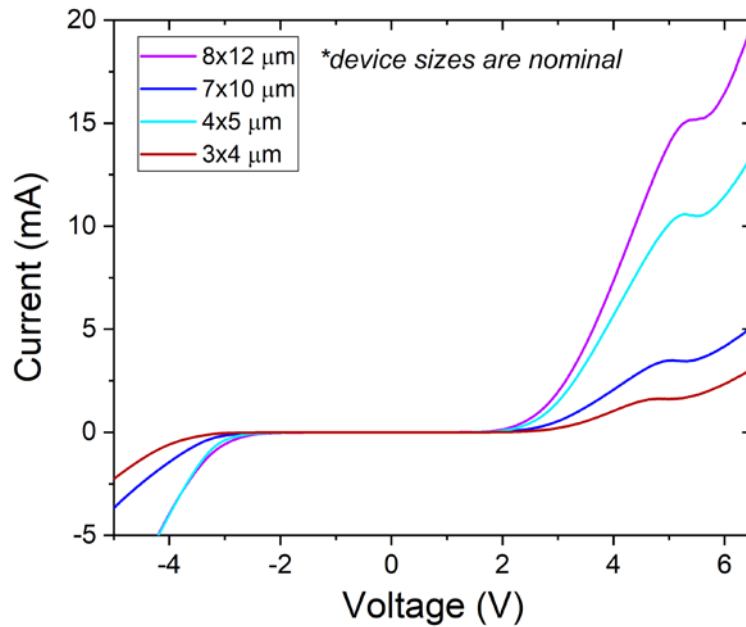


Figure 2. Room-temperature current-voltage curves from RTDs grown at 760 °C GaN-templated sapphire. The nominal device areas are shown in the inset. The NDR regions appear at $\sim 5\text{V}$.